

Bae Ho Park

List of Publications by Year in descending order

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199
papers

10,658
citations

53794

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h-index

32842

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199
docs citations

199
times ranked

10801
citing authors

#	ARTICLE	IF	CITATIONS
1	Progressive and Stable Synaptic Plasticity with Femtojoule Energy Consumption by the Interface Engineering of a Metal/Ferroelectric/Semiconductor. <i>Advanced Science</i> , 2022, 9, .	11.2	7
2	Ion-Movement-Based Synaptic Device for Brain-Inspired Computing. <i>Nanomaterials</i> , 2022, 12, 1728.	4.1	4
3	Gate-tunable photodetector and ambipolar transistor implemented using a graphene/MoSe ₂ barristor. <i>NPG Asia Materials</i> , 2021, 13, .	7.9	18
4	Semiconductor-less vertical transistor with ION/IOFF of 106. <i>Nature Communications</i> , 2021, 12, 1000.	12.8	18
5	Charge-trapping memory device based on a heterostructure of MoS ₂ and CrPS ₄ . <i>Journal of the Korean Physical Society</i> , 2021, 78, 816-821.	0.7	5
6	Interpreting the Entire Connectivity of Individual Neurons in Micropatterned Neural Culture With an Integrated Connectome Analyzer of a Neuronal Network (iCANN). <i>Frontiers in Neuroanatomy</i> , 2021, 15, 746057.	1.7	9
7	Engineering ferromagnetic lines in graphene by local oxidation and hydrogenation using nanoscale lithography. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 074002.	2.8	1
8	Large Temperature-Independent Magnetoresistance without Gating Operation in Monolayer Graphene. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 53134-53140.	8.0	1
9	Understanding filamentary growth and rupture by Ag ion migration through single-crystalline 2D layered CrPS ₄ . <i>NPG Asia Materials</i> , 2020, 12, .	7.9	9
10	Anteroposterior Wnt-RA Gradient Defines Adhesion and Migration Properties of Neural Progenitors in Developing Spinal Cord. <i>Stem Cell Reports</i> , 2020, 15, 898-911.	4.8	10
11	Electrical Properties of MoS ₂ Field-Effect Transistors in Contact with Layered CrPS ₄ . <i>Journal of the Korean Physical Society</i> , 2020, 76, 731-735.	0.7	1
12	Nanotribology of 2D materials and their macroscopic applications. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 393001.	2.8	14
13	Ripples, Wrinkles, and Crumples in Folded Graphene. <i>Journal of the Korean Physical Society</i> , 2020, 76, 985-990.	0.7	1
14	Temperature dependence of tunneling current in Pt/Nb:SrTiO ₃ Schottky junction. <i>Applied Physics Letters</i> , 2020, 116, 022901.	3.3	1
15	Synaptic devices based on two-dimensional layered single-crystal chromium thiophosphate (CrPS ₄). <i>NPG Asia Materials</i> , 2018, 10, 23-30.	7.9	48
16	Dynamic mechanical control of local vacancies in NiO thin films. <i>Nanotechnology</i> , 2018, 29, 275709.	2.6	8
17	Enhanced Metal-Insulator Transition Performance in Scalable Vanadium Dioxide Thin Films Prepared Using a Moisture-Assisted Chemical Solution Approach. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 8341-8348.	8.0	34
18	Effect of oxygen content of the LaAlO ₃ layer on the synaptic behavior of Pt/LaAlO ₃ /Nb-doped SrTiO ₃ memristors for neuromorphic applications. <i>Solid-State Electronics</i> , 2018, 140, 139-143.	1.4	26

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19	Universality of strain-induced anisotropic friction domains on 2D materials. NPG Asia Materials, 2018, 10, 1069-1075.	7.9	17
20	Physical Issues and Applications of Resistive Switching Phenomena. Journal of the Korean Physical Society, 2018, 73, 852-857.	0.7	0
21	Enhanced Performance of Field-Effect Transistors Based on Black Phosphorus Channels Reduced by Galvanic Corrosion of Al Overlayers. ACS Applied Materials & Interfaces, 2018, 10, 18895-18901.	8.0	9
22	Synaptic Plasticity Selectively Activated by Polarization-Dependent Energy-Efficient Ion Migration in an Ultrathin Ferroelectric Tunnel Junction. Nano Letters, 2017, 17, 1949-1955.	9.1	79
23	Accurate and Precise Determination of Mechanical Properties of Silicon Nitride Beam Nanoelectromechanical Devices. ACS Applied Materials & Interfaces, 2017, 9, 7282-7287.	8.0	6
24	Ferroelectric BiFeO ₃ /TiO ₂ nanotube heterostructures for enhanced photoelectrochemical performance. Current Applied Physics, 2017, 17, 679-683.	2.4	17
25	Flexible resistive random access memory devices by using NiO _x /GaN microdisk arrays fabricated on graphene films. Nanotechnology, 2017, 28, 205202.	2.6	12
26	Brownmillerite thin films as fast ion conductors for ultimate-performance resistance switching memory. Nanoscale, 2017, 9, 10502-10510.	5.6	37
27	Intrinsic defect-mediated conduction and resistive switching in multiferroic BiFeO ₃ thin films epitaxially grown on SrRuO ₃ bottom electrodes. Applied Physics Letters, 2016, 108, .	3.3	33
28	Direct Observation of Domain Motion Synchronized with Resistive Switching in Multiferroic Thin Films. ACS Applied Materials & Interfaces, 2016, 8, 35464-35471.	8.0	3
29	Tunneling transport of mono- and few-layers magnetic van der Waals MnPS ₃ . APL Materials, 2016, 4, .	5.1	54
30	Real-time device-scale imaging of conducting filament dynamics in resistive switching materials. Scientific Reports, 2016, 6, 27451.	3.3	9
31	Lead-free piezoelectric BiFeO ₃ -BaTiO ₃ thin film with high Curie temperature. Current Applied Physics, 2016, 16, 1449-1452.	2.4	12
32	Reduced distributions of the set current and the voltage of unipolar resistance switching in a current-biased set process. Journal of the Korean Physical Society, 2016, 68, 1467-1471.	0.7	2
33	Role of fatty acid composites in the toxicity of titanium dioxide nanoparticles used in cosmetic products. Journal of Toxicological Sciences, 2016, 41, 533-542.	1.5	16
34	Selector-free resistive switching memory cell based on BiFeO ₃ nano-island showing high resistance ratio and nonlinearity factor. Scientific Reports, 2016, 6, 23299.	3.3	45
35	Large linear magnetoresistance in heavily-doped Nb:SrTiO ₃ epitaxial thin films. Scientific Reports, 2016, 6, 34295.	3.3	12
36	High piezoelectric performance of lead-free BiFeO ₃ -BaTiO ₃ thin films grown by a pulsed laser deposition method. RSC Advances, 2016, 6, 106899-106903.	3.6	8

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37	Epitaxial Brownmillerite Oxide Thin Films for Reliable Switching Memory. ACS Applied Materials & Interfaces, 2016, 8, 7902-7911.	8.0	72
38	The "self spin valve" in oxygen stoichiometric SrRu _{1-x} Fe _x O ₃ epitaxial thin films. Journal of Alloys and Compounds, 2016, 657, 224-230.	5.5	7
39	Fabricating in-plane transistor and memory using atomic force microscope lithography towards graphene system on chip. Carbon, 2016, 96, 223-228.	10.3	14
40	Reversible quenching of luminescence in ZnO films by electric field action. Physica Status Solidi - Rapid Research Letters, 2015, 9, 307-311.	2.4	1
41	Carrier Transport Properties of Bilayer Graphene Obtained via Hall Measurements. Journal of Nanoscience and Nanotechnology, 2015, 15, 7482-7485.	0.9	0
42	Engineering Optical and Electronic Properties of WS ₂ by Varying the Number of Layers. ACS Nano, 2015, 9, 6854-6860.	14.6	105
43	Enhancement of resistive switching under confined current path distribution enabled by insertion of atomically thin defective monolayer graphene. Scientific Reports, 2015, 5, 11279.	3.3	10
44	Graphene/Pentacene Barristor with Ion-Gel Gate Dielectric: Flexible Ambipolar Transistor with High Mobility and On/Off Ratio. ACS Nano, 2015, 9, 7515-7522.	14.6	46
45	A new simple method for point contact Andreev reflection (PCAR) using a self-aligned atomic filament in transition-metal oxides. Nanoscale, 2015, 7, 8531-8535.	5.6	5
46	Configuration of ripple domains and their topological defects formed under local mechanical stress on hexagonal monolayer graphene. Scientific Reports, 2015, 5, 9390.	3.3	10
47	Effects of the fluctuation in a singly-connected conducting filament structure on the distribution of the reset parameters in unipolar resistance switching. Applied Physics Letters, 2015, 106, 133503.	3.3	4
48	Sample rotation angle dependence of graphene thickness measured using atomic force microscope. Carbon, 2015, 81, 210-215.	10.3	3
49	Electrical control of nanoscale functionalization in graphene by the scanning probe technique. NPG Asia Materials, 2014, 6, e102-e102.	7.9	29
50	Controlled mechanical modification of manganite surface with nanoscale resolution. Nanotechnology, 2014, 25, 475302.	2.6	8
51	Effect of A-site Excess on the Piezoelectric Properties of (K _{0.48} Na _{0.52}) _{1+x} (Nb _{0.55} Ta _{0.45})O _{3.6} Thin Films. Ferroelectrics, 2014, 465, 60-67.		
52	Resistance switching in epitaxial SrCoO _x thin films. Applied Physics Letters, 2014, 105, .	3.3	45
53	Near-band-edge photoluminescence from ZnO film: Negative thermal quenching and role of adsorbed oxygen. Journal of the Korean Physical Society, 2014, 64, 1-5.	0.7	3
54	Improved Ion-Selective Detection Method Using Nanopipette with Poly(vinyl chloride)-Based Membrane. Journal of Physical Chemistry B, 2014, 118, 5130-5134.	2.6	9

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55	Nanopipette exploring nanoworld. Nano Convergence, 2014, 1, 17.	12.1	19
56	Effects of near-surface defects on the optical, electrical and magnetic properties of ZnO films. Journal of the Korean Physical Society, 2014, 64, 1590-1594.	0.7	0
57	Correlation between micrometer-scale ripple alignment and atomic-scale crystallographic orientation of monolayer graphene. Scientific Reports, 2014, 4, 7263.	3.3	21
58	Effect of concentration gradient on ionic current rectification in polyethyleneimine modified glass nano-pipettes. Scientific Reports, 2014, 4, 4005.	3.3	26
59	Ultra-thin resistive switching oxide layers self-assembled by field-induced oxygen migration (FIOM) technique. Scientific Reports, 2014, 4, 6871.	3.3	6
60	Nanotribological Properties of Fluorinated, Hydrogenated, and Oxidized Graphenes. Tribology Letters, 2013, 50, 137-144.	2.6	123
61	Enhanced piezoelectric properties of lead-free 0.935(Bi0.5Na0.5)TiO3-0.065BaTiO3 thin films fabricated by using pulsed laser deposition. Journal of the Korean Physical Society, 2013, 62, 1031-1034.	0.7	7
62	Mechanical Control of Electroresistive Switching. Nano Letters, 2013, 13, 4068-4074.	9.1	55
63	Kinetics of nanodomain growth in ferroelectric artificial superlattices. Scripta Materialia, 2013, 69, 501-504.	5.2	0
64	Scaling Effect on Unipolar and Bipolar Resistive Switching of Metal Oxides. Scientific Reports, 2013, 3, 1657.	3.3	87
65	Large Resistive Switching in Ferroelectric BiFeO ₃ Nano-Island Based Switchable Diodes. Advanced Materials, 2013, 25, 2339-2343.	21.0	192
66	Acceleration of Poly(L-Lactide) Degradation by TiO ₂ Nanoparticles in Sunlight. Journal of Nanoscience and Nanotechnology, 2013, 13, 6983-6987.	0.9	4
67	Characterization of 12CaO·7Al ₂ O ₃ Doped Indium Tin Oxide Films for Transparent Cathode in Top-Emission Organic Light-Emitting Diodes. Journal of Nanoscience and Nanotechnology, 2013, 13, 7556-7560.	0.9	6
68	The Effect of Plasma Treatment on the Physical Properties of SrRuO ₃ Films on SrTiO ₃ Substrate. Journal of the Physical Society of Japan, 2013, 82, 013706.	1.6	6
69	Switchable Schottky diode characteristics induced by electroforming process in Mn-doped ZnO thin films. Applied Physics Letters, 2013, 102, .	3.3	20
70	Carrier type dependence on spatial asymmetry of unipolar resistive switching of metal oxides. Applied Physics Letters, 2013, 103, .	3.3	24
71	Between Scylla and Charybdis: Hydrophobic Graphene-Guided Water Diffusion on Hydrophilic Substrates. Scientific Reports, 2013, 3, 2309.	3.3	60
72	Correlative Multimodal Probing of Ionically-Mediated Electromechanical Phenomena in Simple Oxides. Scientific Reports, 2013, 3, 2924.	3.3	34

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73	Detection of Single Nucleotide Polymorphisms Using a Biosensor-Containing Titanium-Well Array. <i>Journal of Nanoscience and Nanotechnology</i> , 2013, 13, 139-143.	0.9	2
74	Ion-Selective Detection by Plasticized Poly(vinyl chloride) Membrane in Glass Nanopipette with Alternating Voltage Modulation. <i>Journal of Nanoscience and Nanotechnology</i> , 2013, 13, 5413-5419.	0.9	3
75	Facile characterization of ripple domains on exfoliated graphene. <i>Review of Scientific Instruments</i> , 2012, 83, 073905.	1.3	27
76	The role of zinc vacancies in bipolar resistance switching of Ag/ZnO/Pt memory structures. <i>Nanotechnology</i> , 2012, 23, 375201.	2.6	9
77	Development of Beetle-Type Robot with Sub-Micropipette Probe. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 08KB12.	1.5	3
78	Direct observation of potassium ions in HeLa cell with ion-selective nano-pipette probe. <i>Journal of Applied Physics</i> , 2012, 111, 044702.	2.5	17
79	Nano-domain engineering in ultrashort-period ferroelectric superlattices. <i>Applied Physics Letters</i> , 2012, 100, 222906.	3.3	6
80	Investigation of vertically trapped charge locations in Cr-doped-SrTiO ₃ -based charge trapping memory devices. <i>Journal of Applied Physics</i> , 2012, 112, 074505.	2.5	1
81	Coexistence of bi-stable memory and mono-stable threshold resistance switching phenomena in amorphous NbO _x films. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	40
82	Effects of a Load Resistor on Conducting Filament Characteristics and Unipolar Resistive Switching Behaviors in a Pt/NiO/Pt Structure. <i>IEEE Electron Device Letters</i> , 2012, 33, 881-883.	3.9	16
83	Confining grains of textured Cu ₂ O films to single-crystal nanowires and resultant change in resistive switching characteristics. <i>Nanoscale</i> , 2012, 4, 2029.	5.6	31
84	Dual Defects of Cation and Anion in Memristive Nonvolatile Memory of Metal Oxides. <i>Journal of the American Chemical Society</i> , 2012, 134, 2535-2538.	13.7	44
85	Realization of One-Diode-Type Resistive-Switching Memory with Cr-SrTiO ₃ Film. <i>Applied Physics Express</i> , 2012, 5, 091202.	2.4	20
86	Prominent Thermodynamical Interaction with Surroundings on Nanoscale Memristive Switching of Metal Oxides. <i>Nano Letters</i> , 2012, 12, 5684-5690.	9.1	40
87	Influence of MnO clusters on resistance switching behaviors in ZnO/n-Si structures. <i>Journal of the Korean Physical Society</i> , 2012, 60, 1531-1534.	0.7	0
88	Electrical properties of thin films deposited with MnO- and MnO ₂ -modified BiFeO ₃ oxide targets. <i>Journal of the Korean Physical Society</i> , 2012, 61, 1070-1074.	0.7	5
89	Thickness-dependent resistance switching in Cr-doped SrTiO ₃ . <i>Journal of the Korean Physical Society</i> , 2012, 61, 754-758.	0.7	1
90	Ion Current Oscillation in Glass Nanopipettes. <i>Journal of Physical Chemistry C</i> , 2012, 116, 14857-14862.	3.1	7

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91	Characteristics and effects of diffused water between graphene and a SiO ₂ substrate. Nano Research, 2012, 5, 710-717.	10.4	91
92	Selective Measurement of Calcium and Sodium Ion Conductance Using Sub-Micropipette Probes with Ion Filters. Applied Physics Express, 2012, 5, 027001.	2.4	4
93	Self-renewal of embryonic stem cells through culture on nanopattern polydimethylsiloxane substrate. Biomaterials, 2012, 33, 5206-5220.	11.4	47
94	Enhancement of the Raman scattering intensity in folded bilayer graphene. Journal of the Korean Physical Society, 2012, 60, 1278-1281.	0.7	4
95	Development of Beetle-Type Robot with Sub-Micropipette Probe. Japanese Journal of Applied Physics, 2012, 51, 08KB12.	1.5	1
96	A Simple Device Unit Consisting of All NiO Storage and Switch Elements for Multilevel Terabit Nonvolatile Random Access Memory. ACS Applied Materials & Interfaces, 2011, 3, 4475-4479.	8.0	26
97	Self-separated PZT thick films with bulk-like piezoelectric and electromechanical properties. Journal of Materials Research, 2011, 26, 1431-1435.	2.6	13
98	Spatial Nonuniformity in Resistive-Switching Memory Effects of NiO. Journal of the American Chemical Society, 2011, 133, 12482-12485.	13.7	46
99	Intrinsic Mechanisms of Memristive Switching. Nano Letters, 2011, 11, 2114-2118.	9.1	110
100	Friction Anisotropy-Driven Domain Imaging on Exfoliated Monolayer Graphene. Science, 2011, 333, 607-610.	12.6	284
101	Nanoscale Lithography on Monolayer Graphene Using Hydrogenation and Oxidation. ACS Nano, 2011, 5, 6417-6424.	14.6	138
102	Enhanced piezoelectric properties of Ta substituted-(K _{0.5} Na _{0.5})NbO ₃ films: A candidate for lead-free piezoelectric thin films. Journal of Alloys and Compounds, 2011, 509, L194-L198.	5.5	39
103	Growth Behavior and Electrical Properties of a (Na _{0.5} K _{0.5})NbO ₃ Thin Film Deposited on a Pt/Ti/SiO ₂ /Si Substrate Using RF Magnetron Sputtering. Journal of the American Ceramic Society, 2011, 94, 1970-1973.	3.8	26
104	Multiscale simulation on electromigration of the oxygen vacancies in metal oxides. Applied Physics A: Materials Science and Processing, 2011, 102, 909-914.	2.3	6
105	Strain Mismatch Induced Tilted Heteroepitaxial (000 <i>l</i>) Hexagonal ZnO Films on (001) Cubic Substrates. Advanced Engineering Materials, 2011, 13, 1142-1145.	3.5	1
106	Separate Detection of Sodium and Potassium Ions with Sub-micropipette Probe. Japanese Journal of Applied Physics, 2011, 50, 08LB13.	1.5	7
107	High-speed and low-voltage performance in a charge-trapping flash memory using a NiO tunnel junction. Journal Physics D: Applied Physics, 2011, 44, 155105.	2.8	6
108	Unipolar resistive switching mechanism speculated from irreversible low resistance state of Cu ₂ O films. Applied Physics Letters, 2011, 99, 052105.	3.3	20

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109	Resistive switching behaviors of NiO films with controlled number of conducting filaments. Applied Physics Letters, 2011, 98, 192104.	3.3	26
110	Memristor Behaviors of Highly Oriented Anatase TiO ₂ Film Sandwiched between Top Pt and Bottom SrRuO ₃ Electrodes. Applied Physics Express, 2011, 4, 041101.	2.4	17
111	DIELECTRIC PROPERTIES OF EPITAXIAL Ba _{1-x} Sr _x TiO ₃ FILMS ON MgO SUBSTRATES. Functional Materials Letters, 2011, 04, 41-44.	1.2	4
112	EFFECTS OF ARGON+ ION BOMBARDMENT ON A PLATINUM/ZIRCONIUM DIOXIDE/IRIDIUM RESISTIVE SWITCHING MEMORY CELL. Functional Materials Letters, 2011, 04, 71-74.	1.2	2
113	Correlation between Resistance Switching States and Photoluminescence Emission in ZnO Films. Applied Physics Express, 2011, 4, 075801.	2.4	2
114	NANO-PIPETTE PROBE WITH SEPARATIVE ION DETECTION. , 2011, , .		1
115	Leakage Transport in the High-resistance State of a Resistive-switching NbO _x Thin Film Prepared by Pulsed Laser Deposition. Journal of the Korean Physical Society, 2011, 59, 2778-2781.	0.7	21
116	Separate Detection of Sodium and Potassium Ions with Sub-micropipette Probe. Japanese Journal of Applied Physics, 2011, 50, 08LB13.	1.5	8
117	FABRICATION OF GRAPHENE OXIDE USING LOCAL ANODIC OXIDATION BY ATOMIC FORCE MICROSCOPY. , 2011, , .		0
118	Dynamics of resistance switching induced by charge carrier fluence. Journal of Applied Physics, 2010, 108, 074101.	2.5	2
119	Layer-to-island growth of electrodeposited Cu ₂ O films and filamentary switching in single-channeled grain boundaries. Journal of Applied Physics, 2010, 107, .	2.5	15
120	Different nonvolatile memory effects in epitaxial Pt/PbZr _{0.3} Ti _{0.7} O ₃ /LSCO heterostructures. Applied Physics Letters, 2010, 96, .	3.3	24
121	Electrically induced conducting nanochannels in an amorphous resistive switching niobium oxide film. Applied Physics Letters, 2010, 97, 233509.	3.3	42
122	Defect-related room-temperature ferroelectricity in tensile-strained SrTiO ₃ thin films on GdScO ₃ (110) substrates. Applied Physics Letters, 2010, 97, .	3.3	17
123	Direct investigation on conducting nanofilaments in single-crystalline Ni/NiO core/shell nanodisk arrays. Applied Physics Letters, 2010, 96, 053112.	3.3	18
124	Resistive-Switching Memory Effects of NiO Nanowire/Metal Junctions. Journal of the American Chemical Society, 2010, 132, 6634-6635.	18.7	125
125	Resistive Switching Multistate Nonvolatile Memory Effects in a Single Cobalt Oxide Nanowire. Nano Letters, 2010, 10, 1359-1363.	9.1	239
126	Resistive switching transition induced by a voltage pulse in a Pt/NiO/Pt structure. Applied Physics Letters, 2010, 97, .	3.3	65

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127	Ferroelectric and piezoelectric properties of Na _{0.52} K _{0.48} NbO ₃ thin films prepared by radio frequency magnetron sputtering. Applied Physics Letters, 2009, 94, .	3.3	65
128	Magnetic phase coupled to an electric memory state in d oxide ZrO ₂ films. Applied Physics Letters, 2009, 95, .	3.3	3
129	Electrochemical growth and resistive switching of flat-surfaced and (111)-oriented Cu ₂ O films. Applied Physics Letters, 2009, 95, 092108.	3.3	31
130	BaTiO ₃ Doped Na _{0.5} K _{0.5} NbO ₃ Thin Films Deposited by Using Eclipse Shutter Enhanced Pulsed Laser Deposition Method. Journal of Nanoscience and Nanotechnology, 2009, 9, 7354-8.	0.9	0
131	Raman Spectroscopy of Graphene (abstract). , 2009, , .		0
132	Time-dependent electroforming in NiO resistive switching devices. Applied Physics Letters, 2009, 95, .	3.3	40
133	Resistance States and Photoluminescence in Anodic Oxide Alumina Films. Electrochemical and Solid-State Letters, 2009, 12, G47.	2.2	0
134	Mimicking a Superhydrophobic Insect Wing by Argon and Oxygen Ion Beam Treatment on Polytetrafluoroethylene Film. Journal of Bionic Engineering, 2009, 6, 365-370.	5.0	28
135	Agarose and gellan as morphology-directing agents for the preparation of selenium nanowires in water. Carbohydrate Research, 2009, 344, 260-262.	2.3	13
136	Synthesis of selenium nanowires morphologically directed by Shinorhizobial oligosaccharides. Carbohydrate Research, 2009, 344, 1230-1234.	2.3	11
137	The effect of K and Na excess on the ferroelectric and piezoelectric properties of K _{0.5} Na _{0.5} NbO ₃ thin films. Journal Physics D: Applied Physics, 2009, 42, 215304.	2.8	114
138	Interference effect on Raman spectrum of graphene on SiO_2 . Physical Review B, 2009, 80, .	3.2	255
139	Resistance switching memory devices constructed on plastic with solution-processed titanium oxide. Journal of Materials Chemistry, 2009, 19, 2082.	6.7	45
140	Electrical Manipulation of Nanofilaments in Transition-Metal Oxides for Resistance-Based Memory. Nano Letters, 2009, 9, 1476-1481.	9.1	383
141	Nonpolar Resistance Switching in Anodic Oxide Alumina Films. Japanese Journal of Applied Physics, 2009, 48, 070207.	1.5	5
142	Variations in the Raman Spectrum as a Function of the Number of Graphene Layers. Journal of the Korean Physical Society, 2009, 55, 1299-1303.	0.7	197
143	Influence of Mn-oxide Nanoclusters on the Electric Properties of ZnO:Mn Films. Journal of the Korean Physical Society, 2009, 55, 20-23.	0.7	3
144	Green Synthesis of Silver Nanoparticles by Sinorhizobial Octasaccharide Isolated from Sinorhizobium meliloti. Bulletin of the Korean Chemical Society, 2009, 30, 1651-1654.	1.9	18

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145	Surface characteristics of Ni catalytic films on growth behavior of multi-walled carbon nanotubes. Applied Surface Science, 2008, 254, 4644-4649.	6.1	4
146	Write Current Reduction in Transition Metal Oxide Based Resistance Change Memory. Advanced Materials, 2008, 20, 924-928.	21.0	159
147	High Current Density CuO /InZnO Thin Film Diodes for Cross Point Memory Applications. Advanced Materials, 2008, 20, 3066-3069.	21.0	118
148	Electrostatic force microscopy study on the domain switching properties of the Pb(Zr _{0.2} Ti _{0.8})O ₃ thin films with different crystallographic orientations for the probe-based data storage. Ultramicroscopy, 2008, 108, 1081-1085.	1.9	3
149	Synthesis of single-crystal barium titanate nanorods transformed from potassium titanate nanostructures. Materials Research Bulletin, 2008, 43, 996-1003.	5.2	26
150	Role of structural defects in the unipolar resistive switching characteristics of Pt•NiO•Pt structures. Applied Physics Letters, 2008, 93, .	3.3	76
151	Strong Polarization Dependence of Double-Resonant Raman Intensities in Graphene. Nano Letters, 2008, 8, 4270-4274.	9.1	88
152	Segregation of oxygen vacancy at metal-HfO ₂ interfaces. Applied Physics Letters, 2008, 92, .	3.3	32
153	Growth Mechanism of Shape-Controlled Barium Titanate Nanostructures through Soft Chemical Reaction. Crystal Growth and Design, 2008, 8, 3180-3186.	3.0	32
154	Structural Properties and Resistance-Switching Behavior of Thermally Grown NiO Thin Films. Japanese Journal of Applied Physics, 2008, 47, 1635-1638.	1.5	11
155	Effects of the Crystalline Properties on the Dielectric Performances in Ba _{0.5} Sr _{0.5} TiO ₃ Thin Films. Journal of the Korean Physical Society, 2008, 52, 421-426.	0.7	1
156	Shape-Control of Strontium Titanate Nanostructures by a Surface-Capping Soft Chemical Process. Journal of the Korean Physical Society, 2008, 52, 466-470.	0.7	8
157	Resistive Switching Properties of a Polycrystalline TiO ₂ Memory Cell with a WN Buffer Layer Inserted. Journal of the Korean Physical Society, 2008, 53, 3685-3689.	0.7	6
158	Unipolar Resistive Switching of EuxOy Polycrystalline Films. Journal of the Korean Physical Society, 2008, 53, 700-703.	0.7	5
159	Fabrication and Memory Effect of Zr Nanocrystals Embedded in ZrO ₂ Dielectric Layer. Japanese Journal of Applied Physics, 2007, 46, L1246-L1248.	1.5	9
160	Reversible Resistance Switching Behaviors of Pt/NiO/Pt Structures. Japanese Journal of Applied Physics, 2007, 46, 5205.	1.5	7
161	Decrease in switching voltage fluctuation of Pt•NiO•Pt structure by process control. Applied Physics Letters, 2007, 91, 022112.	3.3	63
162	Investigation on Resistive Memory Switching Mechanism of NiO. Integrated Ferroelectrics, 2007, 93, 90-97.	0.7	0

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163	A Low-Temperature-Grown Oxide Diode as a New Switch Element for High-Density, Nonvolatile Memories. <i>Advanced Materials</i> , 2007, 19, 73-76.	21.0	224
164	Two Series Oxide Resistors Applicable to High Speed and High Density Nonvolatile Memory. <i>Advanced Materials</i> , 2007, 19, 3919-3923.	21.0	407
165	First-principles modeling of resistance switching in perovskite oxide material. <i>Applied Physics Letters</i> , 2006, 89, 042904.	3.3	100
166	Ferroelectricity in Ultrathin PbZrO ₃ /PbTiO ₃ Artificial Superlattices by Scanning Probe Microscopy. <i>Ferroelectrics</i> , 2006, 336, 271-277.	0.6	6
167	Electrode dependence of resistance switching in polycrystalline NiO films. <i>Applied Physics Letters</i> , 2005, 87, 263507.	3.3	95
168	Study of Transport and Dielectric of Resistive Memory States in NiO Thin Film. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1301-L1303.	1.5	35
169	Giant and Stable Conductivity Switching Behaviors in ZrO ₂ Films Deposited by Pulsed Laser Depositions. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L345-L347.	1.5	25
170	Heteroepitaxial Growth and Ferroelectricity of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ Films on n-GaN/Al ₂ O ₃ (0001) Substrates Prepared by Pulsed-Laser Deposition. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 7625-7626.	1.5	3
171	SrFeO ₃ nanoparticles-dispersed SrMoO ₄ insulating thin films deposited from Sr ₂ FeMoO ₆ target in oxygen atmosphere. <i>Applied Physics Letters</i> , 2004, 84, 5037-5039.	3.3	13
172	Deposition of SrFeO ₃ -Dispersed SrMoO ₄ Oxide Thin Films on Si (100) Surface for Spintronic Applications. <i>Integrated Ferroelectrics</i> , 2004, 67, 25-30.	0.7	2
173	Ferroelectric Properties of PbZrO ₃ /PbTiO ₃ Artificial Superlattices by Scanning Probe Microscopy. <i>Integrated Ferroelectrics</i> , 2004, 68, 13-18.	0.7	3
174	The Dielectric Properties of Pb _{0.65} Ba _{0.35} ZrO ₃ Thin Films Applicable to Microwave Tunable Devices. <i>Integrated Ferroelectrics</i> , 2004, 66, 205-211.	0.7	7
175	Reproducible resistance switching in polycrystalline NiO films. <i>Applied Physics Letters</i> , 2004, 85, 5655-5657.	3.3	890
176	Spatial distribution analysis of critical temperature in epitaxial Y-Ba-Cu-O film using variable temperature scanning laser microscopy. <i>IEEE Transactions on Applied Superconductivity</i> , 2003, 13, 2894-2896.	1.7	6
177	Role of atomic arrangements at interfaces on the phase control of epitaxial TiO ₂ films. <i>Applied Physics Letters</i> , 2002, 80, 1174-1176.	3.3	26
178	Enhanced Dielectric Properties of (Ba,Sr)TiO ₃ Thin Films Applicable to Tunable Microwave Devices. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 7222-7225.	1.5	13
179	Imaging transport current distribution in high temperature superconductors using room temperature scanning laser microscope. <i>Review of Scientific Instruments</i> , 2002, 73, 3692-3694.	1.3	12
180	Synthesis of Highly Crystalline and Monodisperse Cobalt Ferrite Nanocrystals. <i>Journal of Physical Chemistry B</i> , 2002, 106, 6831-6833.	2.6	297

#	ARTICLE	IF	CITATIONS
181	A New Candidate Material for Use in Ferroelectric Random Access Memory (Fram). <i>Ferroelectrics</i> , 2002, 267, 121-129.	0.6	3
182	Dielectric response and structural properties of TiO ₂ -doped Ba _{0.6} Sr _{0.4} TiO ₃ films. <i>Applied Physics Letters</i> , 2002, 81, 114-116.	3.3	27
183	Effects of very thin strain layers on dielectric properties of epitaxial Ba _{0.6} Sr _{0.4} TiO ₃ films. <i>Applied Physics Letters</i> , 2001, 78, 533-535.	3.3	164
184	Dielectric properties of Ba _{0.6} Sr _{0.4} TiO ₃ thin films with various strain states. <i>Integrated Ferroelectrics</i> , 2001, 39, 271-280.	0.7	0
185	Structure, processing, and property relationships in tunable rf and microwave devices. <i>Integrated Ferroelectrics</i> , 2001, 39, 261-270.	0.7	3
186	Photovoltaic response and dielectric properties of epitaxial anatase-TiO ₂ films grown on conductive La _{0.5} Sr _{0.5} CoO ₃ electrodes. <i>Applied Physics Letters</i> , 2001, 79, 2797-2799.	3.3	39
187	High nonlinearity of Ba _{0.6} Sr _{0.4} TiO ₃ films heteroepitaxially grown on MgO substrates. <i>Applied Physics Letters</i> , 2000, 77, 2587-2589.	3.3	108
188	Microstructure and dielectric properties of Ba _{1-x} Sr _x TiO ₃ films grown on LaAlO ₃ substrates. <i>Applied Physics Letters</i> , 2000, 77, 1200-1202.	3.3	158
189	Influence of the laser fluence on the electrical properties of pulsed-laser-deposited SrBi ₂ Ta ₂ O ₉ thin films. <i>Applied Physics Letters</i> , 1999, 75, 1155-1157.	3.3	30
190	Different fatigue behaviors of SrBi ₂ Ta ₂ O ₉ and Bi ₃ TiTaO ₉ films: Role of perovskite layers. <i>Applied Physics Letters</i> , 1999, 75, 2644-2646.	3.3	74
191	Far-infrared transmission studies on a superconducting BaPb _{1-x} Bi _x O ₃ thin film: Effects of a carrier scattering rate. <i>Physical Review B</i> , 1999, 59, 8869-8874.	3.2	8
192	Lanthanum-substituted bismuth titanate for use in non-volatile memories. <i>Nature</i> , 1999, 401, 682-684.	27.8	2,119
193	Differences in nature of defects between SrBi ₂ Ta ₂ O ₉ and Bi ₄ Ti ₃ O ₁₂ . <i>Applied Physics Letters</i> , 1999, 74, 1907-1909.	3.3	221
194	Built-in voltages and asymmetric polarization switching in Pb(Zr,Ti)O ₃ thin film capacitors. <i>Applied Physics Letters</i> , 1998, 72, 3380-3382.	3.3	108
195	Nonferroelectric epitaxial SrBi ₂ Ta ₂ O ₉ oxide thin film with a high dielectric constant. <i>Applied Physics Letters</i> , 1998, 73, 2518-2520.	3.3	26
196	Imprint failures and asymmetric electrical properties induced by thermal processes in epitaxial Bi ₄ Ti ₃ O ₁₂ thin films. <i>Journal of Applied Physics</i> , 1998, 84, 4428-4435.	2.5	59
197	Effects of interface charges on imprint of epitaxial Bi ₄ Ti ₃ O ₁₂ thin films. <i>Applied Physics Letters</i> , 1997, 70, 1101-1103.	3.3	52
198	Pulsed laser deposition of Bi ₄ Ti ₃ O ₁₂ thin films and their anomalous imprint characteristics. <i>Integrated Ferroelectrics</i> , 1997, 14, 181-191.	0.7	2

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199	Asymmetric switching and imprint in (La,Sr)CoO ₃ /Pb(Zr,Ti)O ₃ /(La,Sr)CoO ₃ heterostructures. Integrated Ferroelectrics, 1997, 18, 39-48.	0.7	18